

L Number	Hits	Search Text	DB	Time stamp
1	299	((insulat\$3 with upper) same ((silicon adj nitride) or "si.sub.3n.sub.4")) and ((insulat\$3 with lower) same ((silicon adj dioxide) or "sio.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/10 13:42
2	84	((insulat\$3 with upper) same ((silicon adj nitride) or "si.sub.3n.sub.4")) and ((insulat\$3 with lower) same ((silicon adj dioxide) or "sio.sub.2")) and @ad<19950117	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/10 13:44
3	76	((insulat\$3 with upper) same ((silicon adj nitride) or "si.sub.3n.sub.4")) same (open\$3 via hole) and ((insulat\$3 with lower) same ((silicon adj dioxide) or "sio.sub.2")) same (open\$3 via hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/10 15:57
4	10	((insulat\$3 with upper) same ((silicon adj nitride) or "si.sub.3n.sub.4")) same (open\$3 via hole) and ((insulat\$3 with lower) same ((silicon adj dioxide) or "sio.sub.2")) same (open\$3 via hole) and @ad<19950117	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/10 16:03
5	2	"jp 06186578"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/10 14:48
6	2	"jp 07273342"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/10 14:48
7	176	((silicon adj nitride) or "si.sub.3n.sub.4") same (open\$3 via hole) and ((silicon adj dioxide) or "sio.sub.2") same (open\$3 via hole) and lcd	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/10 16:02
8	19	((silicon adj nitride) or "si.sub.3n.sub.4") same (open\$3 via hole) and ((silicon adj dioxide) or "sio.sub.2") same (open\$3 via hole) and lcd and @ad<19950117	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/10 16:04
-	14580	insulat\$3 with upper with lower with layer	USPAT; EPO; JPO; DERWENT	2003/04/10 13:35
-	97664	(multilayer or multilevel or multi-layer or multi-level) and (contact or open\$3 or via or hole)	USPAT; EPO; JPO; DERWENT	2002/04/23 11:16
-	3512	((thin adj film) or tft) and pixel and array and matrix and (liquid adj crystal)	USPAT; EPO; JPO; DERWENT	2002/04/19 13:21
-	32	(insulat\$3 with upper with lower with layer) and ((multilayer or multilevel or multi-layer or multi-level) and (contact or open\$3 or via or hole) and ((thin adj film) or tft) and pixel and array and matrix and (liquid adj crystal))	USPAT; EPO; JPO; DERWENT	2002/04/19 13:13
-	0	((insulat\$3 with upper with lower with layer) and ((multilayer or multilevel or multi-layer or multi-level) and (contact or open\$3 or via or hole) and ((thin adj film) or tft) and pixel and array and matrix and (liquid adj crystal))) and 1994.ay.	USPAT; EPO; JPO; DERWENT	2002/04/19 13:15
-	949	(insulat\$3 with upper with lower with layer) and 1994.ay.	USPAT; EPO; JPO; DERWENT	2002/04/19 13:16
-	6361	((multilayer or multilevel or multi-layer or multi-level) and (contact or open\$3 or via or hole) and 1994.ay.	USPAT; EPO; JPO; DERWENT	2002/04/19 13:16
-	326	((thin adj film) or tft) and pixel and array and matrix and (liquid adj crystal) and 1994.ay.	USPAT; EPO; JPO; DERWENT	2002/04/19 13:16

-	0	((insulat\$3 with upper with lower with layer) and 1994.ay.) and (((multilayer or multilevel or multi-layer or multi-level) and (contact or open\$3 or via or hole)) and 1994.ay.) and (((thin adj film) or tft) and pixel and array and matrix and (liquid adj crystal)) and 1994.ay.)	USPAT; EPO; JPO; DERWENT	2002/04/19 13:16
-	155	((insulat\$3 with upper with lower with layer) and 1994.ay.) and (((multilayer or multilevel or multi-layer or multi-level) and (contact or open\$3 or via or hole)) and 1994.ay.)	USPAT; EPO; JPO; DERWENT	2002/04/19 13:17
-	555	pixel and array and matrix and (liquid adj crystal) and 1994.ay.	USPAT; EPO; JPO; DERWENT	2002/04/19 13:23
-	0	((insulat\$3 with upper with lower with layer) and 1994.ay.) and (((multilayer or multilevel or multi-layer or multi-level) and (contact or open\$3 or via or hole)) and 1994.ay.) ) and (pixel and array and matrix and (liquid adj crystal) and 1994.ay.)	USPAT; EPO; JPO; DERWENT	2002/04/19 13:22
-	3189	pixel and (liquid adj crystal) and 1994.ay.	USPAT; EPO; JPO; DERWENT	2002/04/19 13:23
-	4	((insulat\$3 with upper with lower with layer) and 1994.ay.) and (((multilayer or multilevel or multi-layer or multi-level) and (contact or open\$3 or via or hole)) and 1994.ay.) ) and (pixel and (liquid adj crystal) and 1994.ay.)	USPAT; EPO; JPO; DERWENT	2002/04/19 13:29
-	12	"5814529"	USPAT; EPO; JPO; DERWENT	2002/04/19 13:48
-	2	"6320224"	USPAT; EPO; JPO; DERWENT	2002/04/19 13:48
-	14612	insulat\$3 with upper with lower with layer	USPAT; EPO; JPO; DERWENT	2002/04/23 11:25
-	97866	(multilayer or multilevel or multi-layer or multi-level) and (contact or open\$3 or via or hole)	USPAT; EPO; JPO; DERWENT	2002/04/23 11:31
-	2117	(insulat\$3 with upper with lower with layer) and ((multilayer or multilevel or multi-layer or multi-level) and (contact or open\$3 or via or hole))	USPAT; EPO; JPO; DERWENT	2002/04/23 11:21
-	485	((insulat\$3 with upper with lower with layer) and ((multilayer or multilevel or multi-layer or multi-level) and (contact or open\$3 or via or hole))) and capacitor	USPAT; EPO; JPO; DERWENT	2002/04/23 11:22
-	40612	(multilayer or multilevel or multi-layer or multi-level) same (contact or open\$3 or via or hole)	USPAT; EPO; JPO; DERWENT	2002/04/23 11:23
-	498	(insulat\$3 with upper with lower with layer) same ((multilayer or multilevel or multi-layer or multi-level) same (contact or open\$3 or via or hole))	USPAT; EPO; JPO; DERWENT	2002/04/23 11:23
-	58	((insulat\$3 with upper with lower with layer) same ((multilayer or multilevel or multi-layer or multi-level) same (contact or open\$3 or via or hole))) and capacitor	USPAT; EPO; JPO; DERWENT	2002/04/23 11:24
-	0	((insulat\$3 with upper with lower with layer) same ((multilayer or multilevel or multi-layer or multi-level) same (contact or open\$3 or via or hole))) and capacitor	USPAT; EPO; JPO; DERWENT	2002/04/23 11:25
-	15197083	(insulat\$3 with upper with lower with layer)@ay<96 (insulat\$3 with upper with lower with layer)@ay<1996	USPAT; EPO; JPO; DERWENT	2002/04/23 11:30

-	9466	((insulat\$3 with upper with lower with layer) and @ay<1996	USPAT; EPO; JPO; DERWENT	2002/04/23 11:31
-	26459	((multilayer or multilevel or multi-layer or multi-level) same (contact or open\$3 or via or hole)) and @ay<1996	USPAT; EPO; JPO; DERWENT	2002/04/23 11:33
-	695	((insulat\$3 with upper with lower with layer) and @ay<1996) and ((multilayer or multilevel or multi-layer or multi-level) same (contact or open\$3 or via or hole)) and @ay<1996	USPAT; EPO; JPO; DERWENT	2002/04/23 11:34
-	122	((insulat\$3 with upper with lower with layer) and @ay<1996) and ((multilayer or multilevel or multi-layer or multi-level) same (contact or open\$3 or via or hole)) and @ay<1996)) and capacitor	USPAT; EPO; JPO; DERWENT	2002/04/23 15:35
-	79	((insulat\$3 with upper with lower with layer) and @ay<1996) and ((multilayer or multilevel or multi-layer or multi-level) same (contact or open\$3 or via or hole)) and @ay<1996)) and (silicon adj (nitride and oxide))	USPAT; EPO; JPO; DERWENT	2002/04/24 13:02
-	24	((insulat\$3 with upper with lower with layer) and @ay<1996) and ((multilayer or multilevel or multi-layer or multi-level) same (contact or open\$3 or via or hole)) and @ay<1996)) and (indium adj tin)	USPAT; EPO; JPO; DERWENT	2002/04/24 10:02
-	22	((insulat\$3 with upper with lower with layer) and @ay<1995) and ((multilayer or multilevel or multi-layer or multi-level) same (contact or open\$3 or via or hole)) and @ay<1995)) and (indium adj tin)	USPAT; EPO; JPO; DERWENT	2002/04/24 10:04
-	57	((insulat\$3 with upper with lower with layer) and @ay<1995) and ((multilayer or multilevel or multi-layer or multi-level) same (contact or open\$3 or via or hole)) and @ay<1995)) and (silicon adj (nitride and oxide))	USPAT; EPO; JPO; DERWENT	2002/04/24 13:05
-	0	(dual adj damascene) and @ad<1995	USPAT; EPO; JPO; DERWENT	2002/09/16 13:50
-	13	(dual adj damascene) and @ad<19950117	USPAT; EPO; JPO; DERWENT	2002/09/18 17:11
-	0	(damascene same insulator same stopper same second same mask) and @ad<19950117	USPAT; EPO; JPO; DERWENT	2002/09/16 14:24
-	0	(damascene and insulator and stopper) and (second with mask) and @ad<19950117	USPAT; EPO; JPO; DERWENT	2002/09/16 14:25
-	6	(damascene and insulator) and (second with mask) and @ad<19950117	USPAT; EPO; JPO; DERWENT	2002/09/16 14:39
-	16	damascene and (insulator and (multilevel or multilayer)) and @ad<19950117	USPAT; EPO; JPO; DERWENT	2002/09/16 14:40
-	250	damascene and ((insulator or dielectric) with upper with lower)	USPAT; EPO; JPO; DERWENT	2002/09/16 15:45
-	152	(damascene and ((insulator or dielectric) with upper with lower)) and mask\$3 and etch\$3	USPAT; EPO; JPO; DERWENT	2002/09/16 15:45
-	118	((damascene and ((insulator or dielectric) with upper with lower)) and mask\$3 and etch\$3) and 438/\$3.ccls.	USPAT; EPO; JPO; DERWENT	2002/09/16 15:44
-	95	damascene same ((insulator or dielectric) with upper with lower)	USPAT; EPO; JPO; DERWENT	2002/09/16 15:45
-	52	(damascene same ((insulator or dielectric) with upper with lower)) and mask\$3 and etch\$3 and 438/\$3.ccls.	USPAT; EPO; JPO; DERWENT	2002/09/16 15:45

-	0	((damascene same ((insulator or dielectric) with upper with lower)) and mask\$3 and etch\$3 and 438/\$3.ccls.) and @ad<19950117	USPAT; EPO; JPO; DERWENT	2002/09/16 15:46
-	0	(damascene same ((insulator or dielectric) with upper with lower)) and @ad<19950117	USPAT; EPO; JPO; DERWENT	2002/09/16 15:46
-	1	((damascene and ((insulator or dielectric) with upper with lower)) and mask\$3 and etch\$3) and 438/\$3.ccls.) and @ad<19950117	USPAT; EPO; JPO; DERWENT	2002/09/16 15:48
-	3	(damascene and ((insulator or dielectric) with upper with lower)) and @ad<19950117	USPAT; EPO; JPO; DERWENT	2002/09/16 15:48
-	28	((etch with selectivit\$3) same (insulator or dielectric)) and @ad<19950117) and ((multilayer or multilevel) with (insulator or dielectric))	USPAT; EPO; JPO; DERWENT	2002/09/18 16:40
-	227	((etch with selectivit\$3) same (insulator or dielectric)) and @ad<19950117	USPAT; EPO; JPO; DERWENT	2002/09/18 17:07
-	148	((etch with selectivit\$3) same (insulator or dielectric)) and @ad<19950117) and 438/\$3.ccls.	USPAT; EPO; JPO; DERWENT	2002/09/18 17:07
-	9	(dual adj damascene) and @ad<19950117 and (insulator or dielectric)	USPAT; EPO; JPO; DERWENT	2002/09/18 17:15
-	0	(dual adj damascene) and @ad<19950117 and ((insulator or dielectric) with (multilayer or multilevel))	USPAT; EPO; JPO; DERWENT	2002/09/18 17:15